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FDS6912

Dual N-Channel Logic Level PWM Optimized PowerTrench® MOSFET

General Description

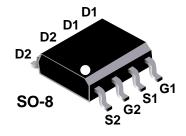
These N-Channel Logic Level MOSFETs have been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

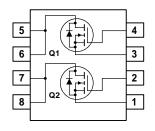
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable RDS(ON) specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 6 A, 30 V. $\begin{aligned} R_{DS(ON)} &= 0.028 \; \Omega \; @ \; V_{GS} = 10 \; V \\ R_{DS(ON)} &= 0.042 \; \Omega \; @ \; V_{GS} = 4.5 \; V. \end{aligned}$
- Optimized for use in switching DC/DC converters with PWM controllers
- · Very fast switching.
- · Low gate charge





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±25	V
I _D	Drain Current - Continuous	(Note 1a)	6	А
	- Pulsed		20	
P _D	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

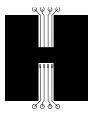
Package Marking and Ordering Information

Device Marking Device		Reel Size	Tape width	Quantity	
FDS6912	FDS6912 FDS6912 13"		12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		20		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \qquad V_{GS} = 0 \text{ V} $ $T_{J} = 55^{\circ}\text{C}$			1 10	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 25 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -25 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	2	3	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		- 5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, \qquad I_{D} = 6 \text{ A} $ $T_{J} = 125^{\circ}\text{C}$		0.024 0.034	0.028 0.048	Ω
		$V_{GS} = 4.5 \text{ V}, \qquad I_D = 4.9 \text{ A}$		0.035	0.042	
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 5 \text{ V}$	20			Α
g FS	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 6 \text{ A}$		20		S
Dynamio	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		740		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		170		pF
C _{rss}	Reverse Transfer Capacitance	7		75		pF
Switchir	ng Characteristics (Note 2)		•	•		
d(on)	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, \qquad I_{D} = 1 \text{ A},$		8	16	ns
r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		13	24	ns
d(off)	Turn-Off Delay Time	7		18	29	ns
f	Turn-Off Fall Time	<u> </u>		8	16	ns
Q_g	Total Gate Charge	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 6 \text{ A},$		7	10	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 5 V		3.8		nC
Q_{gd}	Gate-Drain Charge	7		2.5		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings	•	•		
s	Maximum Continuous Drain-Source				1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 1.3 \text{ A} \text{(Note 2)}$		0.75	1.2	V

Notes

 R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{eJC} is guaranteed by design while R_{eCA} is determined by the user's board design.



a) 78°/W when mounted on a 0.5in² pad of 2 oz copper



b) 125°/W when mounted on a 0.02 in² pad of 2 oz copper

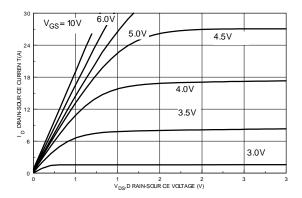


c) 135°/W when mounted on a minimum mounting pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < 300μ s, Duty Cycle < 2.0%

Typical Characteristics

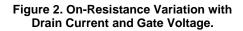


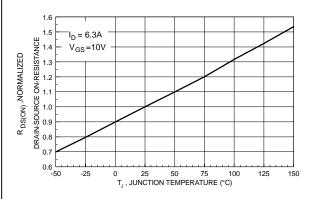
Resistance

Order

Orde

Figure 1. On-Region Characteristics.





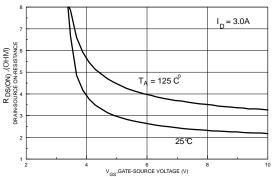
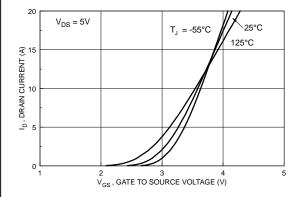


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



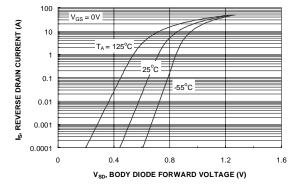
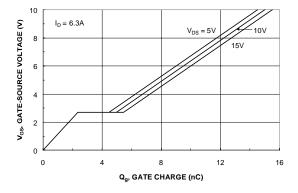


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



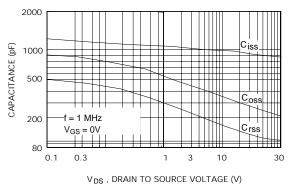
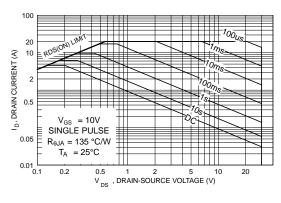


Figure 7. Gate Charge Characteristics.

Figure 8. Capacitance Characteristics.



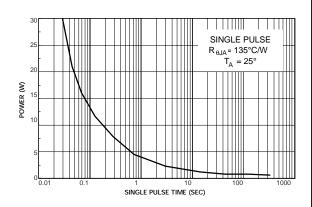


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

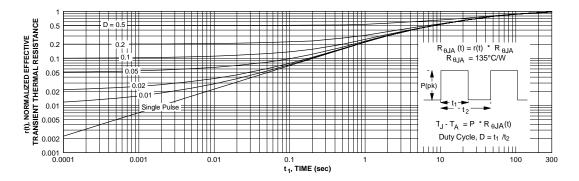


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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